

4.5Ω 300MHz Bandwidth Dual SPDT Analog Switch UM4717 CSP10 1.90×1.40 UM4717Q QFN10 1.80×1.40

General Description

The UM4717/UM4717Q low-voltage, low on-resistance (R_{ON}), dual single-pole/double-throw (SPDT) analog switch operates from a single +1.8V to +5.5V supply. The device is designed for USB 1.1/2.0 and audio switching applications.

The UM4717 features two $4.5\Omega R_{ON}(max)$ SPDT switches with 1.2Ω flatness and 0.3Ω matching between channels, while the UM4717Q features two $6\Omega R_{ON}(max)$ SPDT switches with 1.8Ω flatness and 0.6Ω matching between channels. The switch offers break-before-make switching (1ns) with t_{ON} <80ns and t_{OFF} <40ns at +2.7V. The digital logic inputs are +1.8V logic compatible with a +2.7V to +3.6V supply.

The UM4717 is packaged in a chip-scale package (CSP), occupies only a 1.90mm \times 1.40mm area and has a 4 \times 3 bump array with a bump pitch of 0.50mm. The UM4717Q is packaged in a 1.80mm \times 1.40mm QFN10 package, both significantly reducing the required PC board area.

Applications

- USB 1.1/2.0 Signal Switching Circuits
- Battery-Operated Equipment
- Audio/Video-Signal Routing
- Headphone Switching
- Low-Voltage Data-Acquisition Systems
- Sample-and-Hold Circuits
- Cell Phones
- PDAs

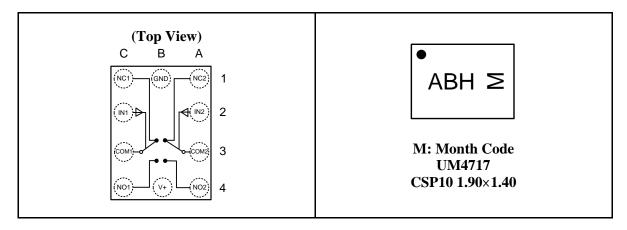
Features

- 2ns (Max) Differential Skew
- -3dB Bandwidth: 300MHz
- Low 15pF On-Channel Capacitance
- Single-Supply Operation from +1.8V to +5.5V
- Typical R_{ON}(max) with +3V Supply: 4.5Ω (UM4717), 6Ω (UM4717Q)
- Rail-to-Rail Signal Handling
- High Off-Isolation: -50dB (10MHz)
- Low Crosstalk: -70dB (10MHz)
- Low Distortion: 0.03%

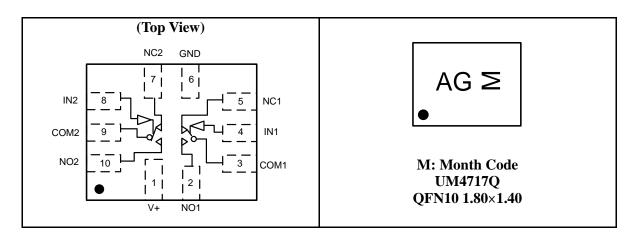
Top View

- +1.8V CMOS-Logic Compatible
- < 0.5nA Leakage Current at +25 °C

Pin Configurations







Ball Mapping for UM4717

С	В	Α	
NC1	GND	NC2	1
IN1		IN2	2
COM1		COM2	3
NO1	V+	NO2	4

Transparent Top View

Pin Description

P	Pin UM4717 UM4717Q		Evention
UM4717			Function
A1	7	NC2	Analog Switch 2-Normally Closed Terminal
A2	8	IN2	Analog Switch 2-Digital Control Input
A3 9		COM2	Analog Switch 2-Common Terminal
A4	10	NO2	Analog Switch 2-Normally Open Terminal
B1	6	GND	Ground Connection
B4	1	V_+	Positive Supply Voltage
C1	5	NC1	Analog Switch 1-Normally Closed Terminal
C2	4	IN1	Analog Switch 1-Digital Control Input
C3 3		COM1	Analog Switch 1-Common Terminal
C4	2	NO1	Analog Switch 1-Normally Open Terminal



Ordering Information

Part Number	Packaging Type	Marking Code	Shipping Qty
UM4717	CSP10 1.90×1.40	ABH	3000pcs/7 Inch Tape & Reel
UM4717Q	QFN10 1.80×1.40	AG	3000pcs/7 Inch Tape & Reel

Function Table

IN_	NO_	NC_	
0	OFF	ON	
1	ON	OFF	

Absolute Maximum Ratings

Symbol	Parameter	Limit	Unit	
V_+	Supply Voltage		-0.3 to +6.0	
Vs	DC Switch Voltage (Note 1)		-0.3 to (V ₊ +0.3)	V
IN_	DC IN Voltage		-0.3 to +6.0	
Io	Continuous Current (COM_, NO_,	, NC_)	± 100	A
I _P	Peak Current (Pulsed at 1ms, 10%	Duty Cycle)	± 200	mA
To	Operating Temperature Range		-40 to +85	
T _J	Junction Temperature		+150	
T _{STG}	Storage Temperature Range		-65 to +150	ംറ
T _L	Junction Lead Temperature (Solde	ring, 10 Seconds)	+300	C
т	Dump Tomporature (Soldaring)	Infrared (15s)	+220	
T _{Bump}	Bump Temperature (Soldering) Vapor Phase (60s)		+215	
P _D	Continuous Power Dissipation @ -	909	mW	
ESD	ESD Method 3015.7		>2000	V

Note 1: Signals on COM_, NO_, or NC_ exceeding V_+ or GND are clamped by internal diodes. Limit forward-diode current to maximum current rating.



Electrical Characteristics (Single +3V Supply)

 $(V_{+}=+2.7V \text{ to } +3.6V, T_{A}=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } V_{+}=+3.0V, T_{A}=+25^{\circ}\text{C}) \text{ (Notes 2, 3)}$

Symbol	Parameter	Test Cond	itions	Тетр	(-4	Limits 0°C to 85	5°C)	Unit
Symbol	r ai ametei	Test Conu	remp	Min	Тур	Max	Umt	
DC Electri	cal Characteristics			•				•
V _{COM} V _{NO} V _{NC}	Analog Signal Range			Full	0		V_+	V
V_+	Power Supply Range			Full	1.8		5.5	V
I_+	Supply Current	V ₊ =+5.5V, V _{IN}	=0V or V ₊	Full			1	μΑ
I _{COM_(ON)}	COM_On Leakage Current (Note 4)	V ₊ =+3.6V, V _{COM} V _{NO} or V _{NC} =0.3 Floatin	3V, 3.3V, or	Room Full	-1 -2	+0.01	+1 +2	nA
I _{OFF}	OFF State Leakage Current (Note 4)	$V_{+}=+3.6V, V_{COM}$ V_{NO} or $V_{NC}=3$	=0.3V, 3.3V;	Room Full	-0.5 -1	+0.01	+0.5 +1	nA
V_{IH}	Input High Voltage			Full	1.6			v
V _{IL}	Input Low Voltage			Full			0.5	v
I _{IN}	Input Leakage Current	V_{+} =+3.6V, $V_{IN_{-}}$	=0 or 5.5V	Full	-100		+100	nA
		$V_{+}=+2.7V,$ $I_{COM}=10mA;$ V_{NO} or $V_{NC}=1.5V$		Room		3.0	4.5	
_			UM4717	Full			5	
R _{ON}	On-Resistance (Note 4)			Room		4.5	6	Ω
		• NC1.0 •	UM4717Q	Full			7	
		N 0 7N	111/1/21/2	Room		0.1	0.3	
ΔR_{ON}	On Resistance Match Between Channels	V ₊ =+2.7V, I _{COM_} =10mA;	UM4717	Full			0.4	Ω
ARON	(Notes 4, 5)	V _{NO_} or V _{NC_} =1.5V	UM47170	Room		0.5	0.6	32
		· NC_ THE ·	01/01/01/17/Q	Full			0.9	
		V ₊ =+2.7V,	UM4717	Room		0.6	1.2	
R _{FLAT}	On Resistance Flatness	I _{COM} _=10mA;	0	Full			1.5	Ω
• FLA1	(Note 6)	$V_{NO_{-}}$ or $V_{NC_{-}}$ = 1.0V, 1.5V, 2.0V	UM4717Q	Room		1.5	1.8	
		, , , ,		Full			2.0	

Note 2: The parts are 100% tested at +25°C only, and guaranteed by design over the specified temperature range.

Note 3: The algebraic convention used in this data sheet is where the most negative value is a minimum and the most positive value is a maximum.

Note 4: Guaranteed by design.

Note 5: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$.

- Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.
- Note 7: Between any two switches.



Electrical Characteristics (Single +3V Supply) (Continued)

(V₊=+2.7V to +3.6V, $T_A=T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at V₊=+3.0V, $T_A=+25$ °C) (Notes 2, 3)

Symbol	Parameter Test Conditions		Тетр	(-4	Limits 0°C to 8	S5°C)	Unit
Symbol	Tarameter	Test conditions	remp	Min	Тур	Max	Cint
AC Electr	ical Characteristics						
t _{ON}	Turn-On Time	$V_{NO_{-}}, V_{NC_{-}}=1.5V;$ $R_{L}=300\Omega, C_{L}=35pF, Figure 1;$ $V_{IH}=1.5V, V_{IL}=0V$	Room Full		40	80 100	ns
t _{OFF}	Turn-Off Time	$V_{NO_{-}}, V_{NC_{-}}=1.5V;$ $R_{L}=300\Omega, C_{L}=35pF, Figure 1;$ $V_{IH}=1.5V, V_{IL}=0V$	Room Full		20	40 50	ns
t _{BBM}	Break Before Make Time (Note 4)	$V_{NO_{-}}, V_{NC_{-}}=1.5V;$ R _L =300Ω, C _L =35pF, Figure 2	$V_{NO_{2}}, V_{NC_{2}}=1.5V;$ Room		8		ns
t _{SKEW}	Skew (Note 4)	R_S =39 Ω , C_L =50pF, Figure 3	Full		0.15	2	ns
Q _{INJ}	Charge Injection	C_L =1.0nF, Figure 4 V_{GEN} =1.5V, R_{GEN} =0 Ω	Room		5		pC
		f=10MHz; $V_{NO_{-}}$, $V_{NC_{-}}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5			-50		15
V _{ISO}	Off Isolation	$f=1MHz; V_{NO}, V_{NC}=1V_{P-P};$ $R_L=50\Omega, C_L=5pF, Figure 5$	Room		-70		dB
V	Crosstalk (Note 7)	f=10MHz; $V_{NO_{-}}$, $V_{NC_{-}}$ =1 V_{P-P} ; R _L =50 Ω , C _L =5pF, Figure 5	Room		-70		dB
V _{CT}	Clossiaik (Note 7)	f=1MHz; V_{NO} , $V_{NC}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5	KOOIII		-90		uв
BW	-3dB Bandwidth	Signal=0dBm, R_L =50 Ω , C_L =5pF, Figure 5	Room		300		MHz
THD	Total Harmonic Distortion	$R_{L} = 600\Omega,$ $V_{COM} = 2V_{P.P}$	Room		0.03		%
Capacitan	ce						
C _{NO_(OFF)} C _{NC (OFF)}	NO_, NC_ Off Capacitance	f=1MHz, Figure 6	Room		9		pF
C _(ON)	Switch On Capacitance	f=1MHz, Figure 6	Room		15		pF

Note 2: The parts are 100% tested at +25°C only, and guaranteed by design over the specified temperature range.

Note 3: The algebraic convention used in this data sheet is where the most negative value is a minimum and the most positive value is a maximum.

Note 4: Guaranteed by design.

Note 5: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$.

Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

Note 7: Between any two switches.



Electrical Characteristics (Single +5V Supply)

(V₊=+4.2V to +5.5V, $T_A=T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at V₊=+5.0V, $T_A=+25$ °C) (Notes 2, 3)

Symbol	Parameter	Test Condition		Тетр	(-4	Limits 0°C to 8	5°C)	Unit
Symbol	r ar ameter	Test Condition	remp	Min	Тур	Max	Umt	
DC Electr	rical Characteristics							
V _{COM} _ V _{NO} _ V _{NC} _	Analog Signal Range			Full	0		V_{+}	V
V_+	Power Supply Range			Full	1.8		5.5	v
I_+	Supply Current	$V_{+}=+5.5V, V_{IN}=0$	OV or V ₊	Full			1	μΑ
I _{COM_(ON)}	COM_On Leakage Current (Note 4)	V_{+} =+5.5V, V_{COM} =1 V_{NO} or V_{NC} =1.0V Floating	.0V, 4.5V; , 4.5V, or	Room Full	-1 -2	+0.01	+1 +2	nA
I _{OFF}	OFF State Leakage Current (Note 4)	V_{+} =+5.5V, V_{COM} =1.0V, 4.5V; V_{NO} or V_{NC} =1.0V, 4.5V		Room Full	-0.5 -1	+0.01	+0.5 +1	nA
V_{IH}	Input High Voltage			Full	2.3			v
V _{IL}	Input Low Voltage						0.8	V
I _{IN}	Input Leakage Current	V ₊ =+5.5V, V _{IN} _=	0 or V_+	Full	-100		+100	nA
			10.4717	Room		1.7	3	
D		V ₊ =+4.2V,	UM4717	Full			3.5	Ω
R _{ON}	On-Resistance (Note 4)	I _{COM} =10mA; V _{NO} or V _{NC} =3.5V		Room		2.5	3.5	
			UM4717Q	Full			4	
			11114717	Room		0.1	0.3	
ΔR_{ON}	On Resistance Match Between Channels	V ₊ =+4.2V, I _{COM} =10mA;	UM4717	Full			0.4	Ω
ΔICON	(Notes 4, 5)	$V_{NO_{\rm O}}$ or $V_{NC_{\rm C}}$ = 3.5V	UM4717Q	Room		0.5	0.6	52
			omini	Full			0.9	
		V ₊ =+4.2V,	UM4717	Room		0.4	1.2	
R _{FLAT}	On Resistance Flatness	I _{COM} =10mA;		Full			1.5	Ω
	(Note 6)	V _{NO} _ or V _{NC} _=1.0V, 2.0V, 3.5V	UM4717Q	Room		0.9	1.2	
				Full			1.5	

Note 2: The parts are 100% tested at +25°C only, and guaranteed by design over the specified temperature range.

Note 3: The algebraic convention used in this data sheet is where the most negative value is a minimum and the most positive value is a maximum.

Note 4: Guaranteed by design.

Note 5: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$.

- Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.
- Note 7: Between any two switches.



Electrical Characteristics (Single +5V Supply) (Continued)

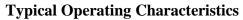
(V₊=+4.2V to +5.5V, $T_A=T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at V₊=+5.0V, $T_A=+25$ °C) (Notes 2, 3)

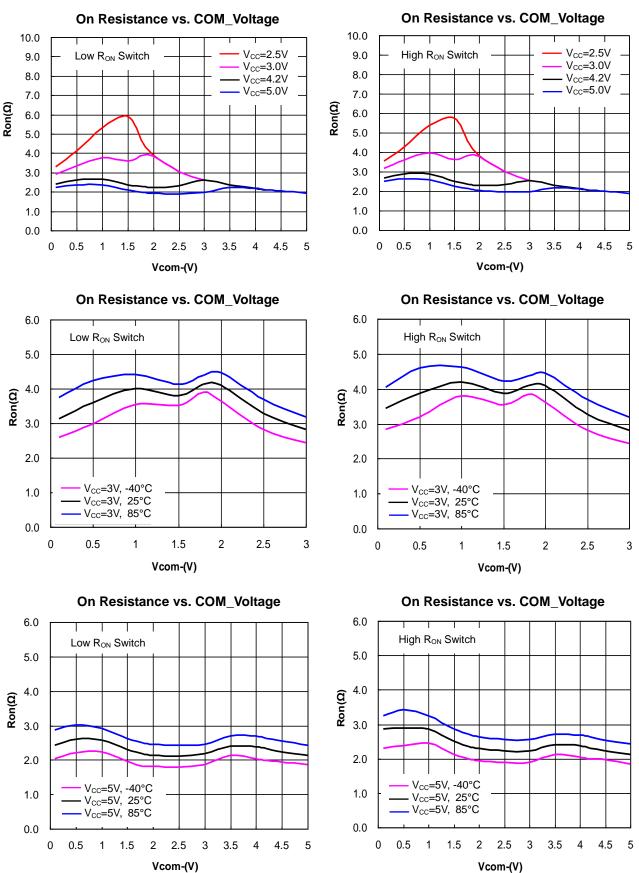
Symbol	Parameter	Test Conditions	Тетр	(-4	Limits)°C to 85	°C)	Unit
Symoor			Tomp	Min	Тур	Max	
AC Electric	cal Characteristics						
t _{ON}	Turn-On Time	$V_{NO_{-}}, V_{NC_{-}}=3.0V;$ R _L =300 Ω , C _L =35pF, Figure 1;	Room Full		30	80 100	ns
t _{OFF}	Turn-Off Time	$V_{NO_{-}}, V_{NC_{-}}=3.0V;$ R _L =300Ω, C _L =35pF, Figure 1;	Room Full		20	40 50	ns
t _{BBM}	Break Before Make Time (Note 4)	$V_{NO_{-}}, V_{NC_{-}}=3.0V;$ R _L =300 Ω , C _L =35pF, Figure 2	Room Full	1	8		ns
t _{SKEW}	Skew (Note 4)	R_S =39 Ω , C_L =50pF, Figure 3	Full		0.15	2	ns
Q _{INJ}	Charge Injection	C_L =1.0nF, Figure 4 V _{GEN} =1.5V, R _{GEN} =0 Ω	Room		9		pC
V	Off Isolation	f=10MHz; $V_{NO_{-}}$, $V_{NC_{-}}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5	- Room		-50		dB
V _{ISO}	On isolation	f=1MHz; V_{NO} , $V_{NC}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5	KOOIII		-70		ub
V	Creastalls (Note 7)	f=10MHz; $V_{NO_{-}}$, $V_{NC_{-}}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5	- Room		-70		dB
V _{CT}	Crosstalk (Note 7)	f=1MHz; V_{NO} , $V_{NC}=1V_{P-P}$; R _L =50 Ω , C _L =5pF, Figure 5	KOOIII		-90		uБ
BW	-3dB Bandwidth	Signal=0dBm, R_L =50 Ω , C_L =5pF, Figure 5	Room		300		MHz
THD	Total Harmonic Distortion	$\begin{array}{c} R_{L} = 600\Omega, \\ V_{COM} = 2V_{P-P} \end{array}$	Room		0.03		%
Capacitanc	e						
C _{NO_(OFF)} C _{NC_(OFF)}	NO_, NC_ Off Capacitance	f=1MHz, Figure 6	Room		9		pF
C _(ON)	Switch On Capacitance	f=1MHz, Figure 6	Room		15		pF

Note 2: The parts are 100% tested at +25°C only, and guaranteed by design over the specified temperature range.

- Note 3: The algebraic convention used in this data sheet is where the most negative value is a minimum and the most positive value is a maximum.
- Note 4: Guaranteed by design.
- Note 5: $\Delta R_{ON} = R_{ON(MAX)} R_{ON(MIN)}$.
- Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.
- Note 7: Between any two switches.

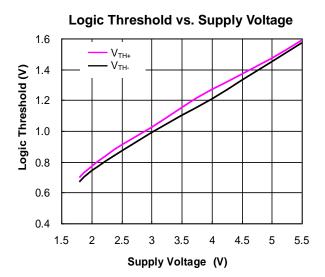


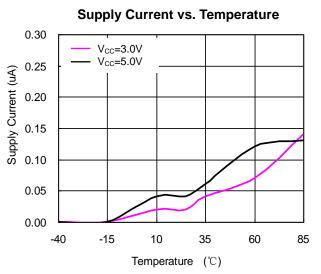


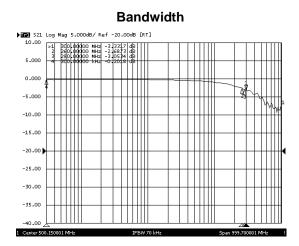




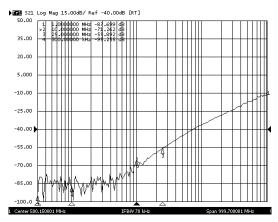
Typical Operating Characteristics (Continued)

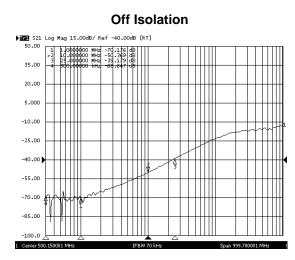






Crosstalk







Detailed Description

The UM4717/UM4717Q high-speed, low-voltage, low on-resistance (R_{ON}), dual SPDT analog switch operates from a single +1.8V to +5.5V supply. The switch features break-before-make switching operation and fast switching speeds (t_{ON} =80ns (max), t_{OFF} =40ns (max)).

The switch has low 15pF on-channel capacitance, which allows for 12Mbps switching of the data signals for USB 1.0/1.1 applications. The UM4717/UM4717Q is designed to switch D_+ and D USB signals with a guaranteed skew of less than 2ns (see Figure 4) as measured from 50% of the input signal to 50% of the output signal.

Applications Information

Digital Control Inputs

The UM4717/UM4717Q logic inputs accept up to +5.5V regardless of supply voltage. For example, with a +3.3V supply, IN_ can be driven low to GND and high to +5.5V allowing for mixing of logic levels in a system. Driving the control logic inputs rail-to-rail minimizes power consumption. For a +3V supply voltage, the logic thresholds are 0.5V (low) and 1.4V (high); for a +5V supply voltage, the logic thresholds are 0.8V (low) and 2.0V (high).

Analog Signal Levels

The on-resistance of the UM4717/UM4717Q changes very little for analog input signals across the entire supply voltage range (see the Typical Operating Characteristics). The switches are bidirectional, so the NO_, NC_, and COM_ pins can be either inputs or outputs.

Power-Supply Sequencing and Over-Voltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Always apply V_+ before applying analog signals, especially if the analog signal is not current-limited.



Test Circuits

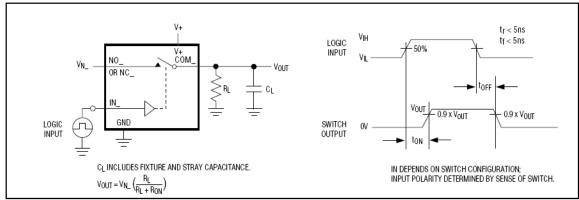


Figure 1. Switching Time

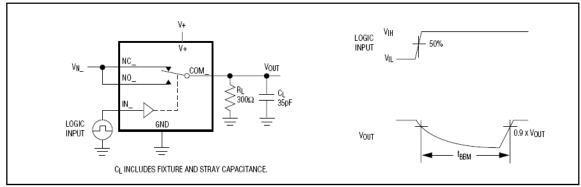


Figure 2. Break-Before-Make Interval



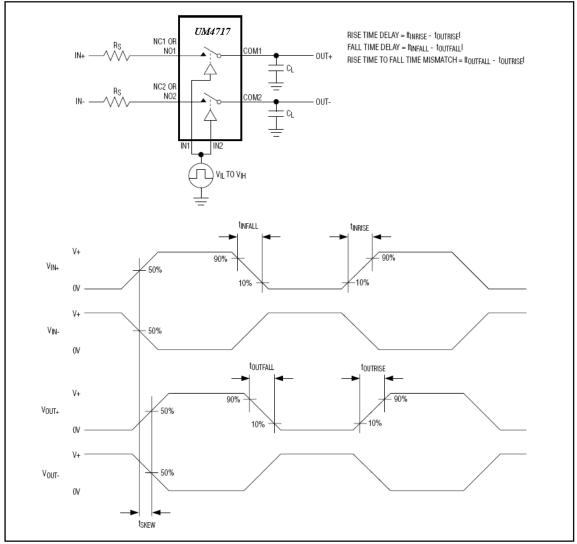


Figure 3. Output Signal Skew

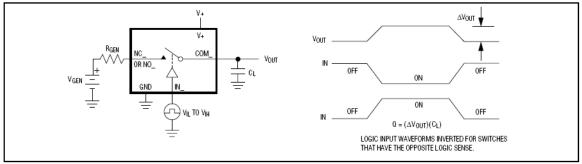


Figure 4. Charge Injection



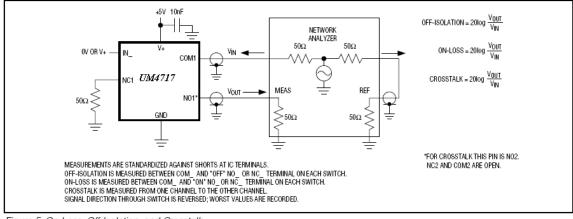


Figure 5. On-Loss, Off-Isolation, and Crosstalk

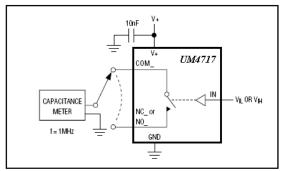


Figure 6. Channel Off/On-Capacitance



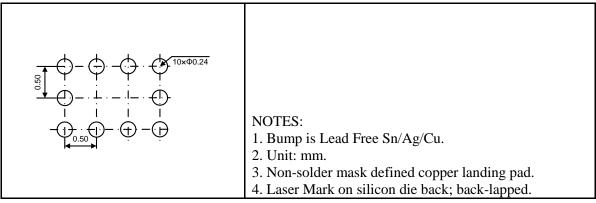
Package Information

UM4717: CSP10 1.90×1.40

Outline Drawing

			DIMENSIONS					
	Le Le L A1 CORNER	S-mak al	MIL	LIMET	ERS		INCHES	
		Symbol	Min	Тур	Max	Min	Тур	Max
ω.	$\bigcirc \bigcirc \bigcirc \bigcirc \bigcirc \blacksquare$	А	-	-	0.68	-	-	0.027
	0 Q O-O-J-I	A1	0.21	0.231	0.24	0.0083	0.0091	0.0094
Top View	► b -	A2	0.40	0.41	0.42	0.015	0.016	0.017
	Boltom view	b	0.27	0.30	0.32	0.011	0.012	0.013
+-00004		D	1.82	-	1.90	0.072	-	0.075
Side View		Е	1.32	-	1.40	0.052	-	0.055
		e		0.50TYI)	(0.020TYP	•

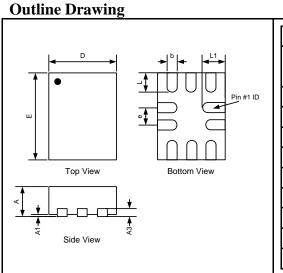
Land Pattern



Tape and Reel Orientation



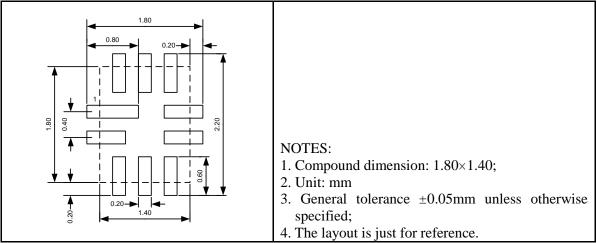




UM4717Q:	OFN10	1.80×1.40
· · · · · · · · · · · · · · · · · · ·	VIII	1.00/1.40

DIMENSIONS							
Symbol	MIL	LIME	TERS	INCHES			
Symbol	Min	Тур	Max	Min	Тур	Max	
А	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0.00	-	0.05	0.000	-	0.002	
A3	().15RE	F	0.006REF			
b	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.35	1.40	1.45	0.053	0.055	0.057	
Е	1.75	1.80	1.85	0.069	0.071	0.073	
e	().40BS	С	C	0.016BS	C	
L	0.30	0.40	0.50	0.012	0.016	0.020	
L1	0.40	0.50	0.60	0.016	0.020	0.024	

Land Pattern



Tape and Reel Orientation





GREEN COMPLIANCE

Union Semiconductor is committed to environmental excellence in all aspects of its operations including meeting or exceeding regulatory requirements with respect to the use of hazardous substances. Numerous successful programs have been implemented to reduce the use of hazardous substances and/or emissions.

All Union components are compliant with the RoHS directive, which helps to support customers in their compliance with environmental directives. For more green compliance information, please visit:

http://www.union-ic.com/index.aspx?cat_code=RoHSDeclaration

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